

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (π-MOSVI)

TPC8002

LITHIUM ION BATTERY

PORTABLE MACHINES AND TOOLS

NOTE BOOK PC

- Low Drain-Source ON Resistance : $R_{DS(ON)} = 11.5\text{ m}\Omega$ (Typ.)
- High Forward Transfer Admittance: $|Y_{fs}| = 15\text{ S}$ (Typ.)
- Low Leakage Current : $I_{DSS} = 10\text{ }\mu\text{A}$ (Max.) ($V_{DS} = 30\text{ V}$)
- Enhancement-Mode : $V_{th} = 0.8\sim 2.0\text{ V}$
($V_{DS} = 10\text{ V}$, $I_D = 1\text{ mA}$)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	30	V
Drain-Gate Voltage ($R_{GS} = 20\text{ k}\Omega$)		V_{DGR}	30	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	DC	I_D	11	A
	Pulse	I_{DP}	44	A
Drain Power Dissipation*** (Ta = 25°C)		P_D	2.4	W
Single Pulse Avalanche Energy**		E_{AS}	157	mJ
Avalanche Current		I_{AR}	11	A
Repetitive Avalanche Energy*		E_{AR}	0.24	mJ
Channel Temperature		T_{ch}	150	°C
Storage Temperature Range		T_{stg}	-55~150	°C

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Ambient***	$R_{th(ch-a)}$	52.1	°C/W

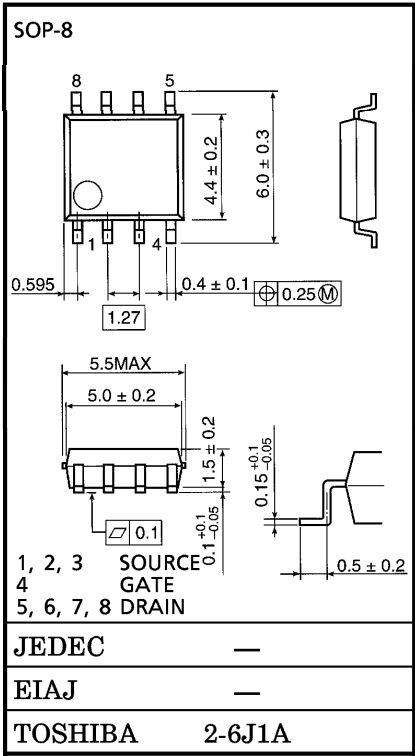
Note ;

- * Repetitive rating ; Pulse Width Limited by Max. Junction temperature.
- ** $V_{DD} = 24\text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 1.0\text{ mH}$, $R_G = 25\text{ }\Omega$, $I_{AR} = 11\text{ A}$
- *** Drive operation ; Mount on glass epoxy board [1 inch² × 0.8 t] (t = 10 s)

This transistor is an electrostatic sensitive device. Please handle with caution.

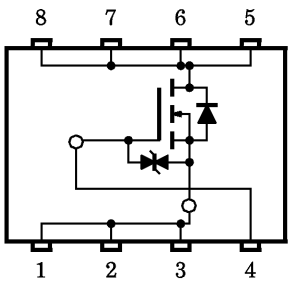
INDUSTRIAL APPLICATIONS

Unit in mm



Weight : 0.08 g

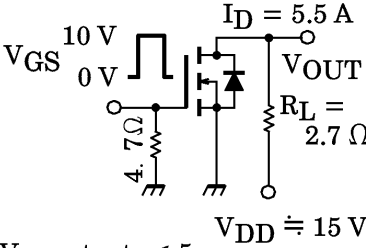
CIRCUIT CONFIGURATION



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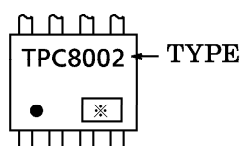
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GSS}	$V_{GS} = \pm 16 \text{ V}$, $V_{DS} = 0 \text{ V}$	—	—	± 10	μA
Drain Cut-Off Current		I_{DSS}	$V_{DS} = 30 \text{ V}$, $V_{GS} = 0 \text{ V}$	—	—	10	μA
Drain-Source Breakdown Voltage		$V_{(BR) DSS}$	$I_D = 10 \text{ mA}$, $V_{GS} = 0 \text{ V}$	30	—	—	V
Gate Threshold Voltage		V_{th}	$V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$	0.8	—	2.0	V
Drain-Source ON Resistance		$R_{DS(ON)}$	$V_{GS} = 4 \text{ V}$, $I_D = 5.5 \text{ A}$	—	19	22	$\text{m}\Omega$
		$R_{DS(ON)}$	$V_{GS} = 10 \text{ V}$, $I_D = 5.5 \text{ A}$	—	12	14	$\text{m}\Omega$
Forward Transfer Admittance		$ Y_{fs} $	$V_{DS} = 10 \text{ V}$, $I_D = 5.5 \text{ A}$	7.5	15	—	S
Input Capacitance		C_{iss}	$V_{DS} = 10 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$	—	1425	—	pF
Reverse Transfer Capacitance		C_{rss}		—	200	—	
Output Capacitance		C_{oss}		—	790	—	
Switching Time	Rise Time	t_r	 V_{GS} 10 V 0 V $I_D = 5.5 \text{ A}$ V_{OUT} $R_L = 2.7 \Omega$ $V_{DD} \doteq 15 \text{ V}$ $V_{IN} : t_r, t_f < 5 \text{ ns}$ Duty $\leq 1\%$, $t_w = 10 \mu\text{s}$	—	11	—	ns
	Turn-On Time	t_{on}		—	19	—	
	Fall Time	t_f		—	25	—	
	Turn-Off Time	t_{off}		—	100	—	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Q_g	$V_{DD} \doteq 24 \text{ V}$, $V_{GS} = 10 \text{ V}$ $I_D = 11 \text{ A}$	—	44	—	nC
Gate-Source Charge		Q_{gs}		—	29	—	
Gate-Drain ("Miller") Charge		Q_{gd}		—	15	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	11	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	44	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = 11 \text{ A}$, $V_{GS} = 0 \text{ V}$	—	—	-1.2	V

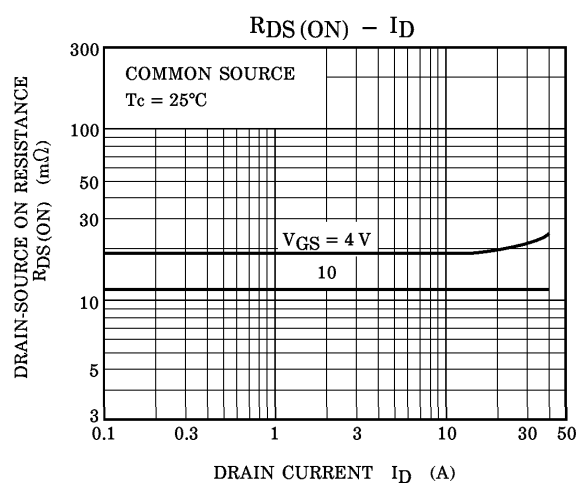
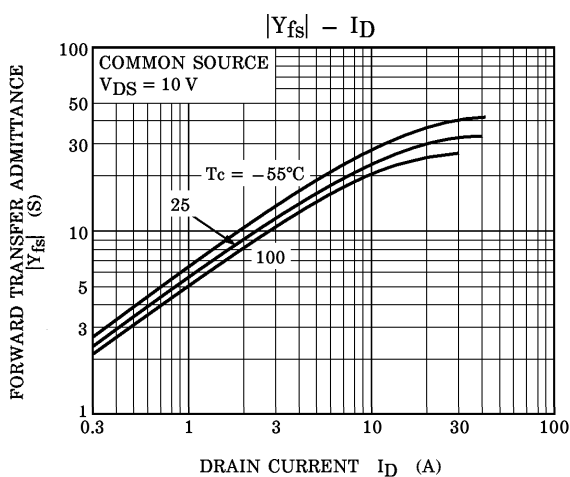
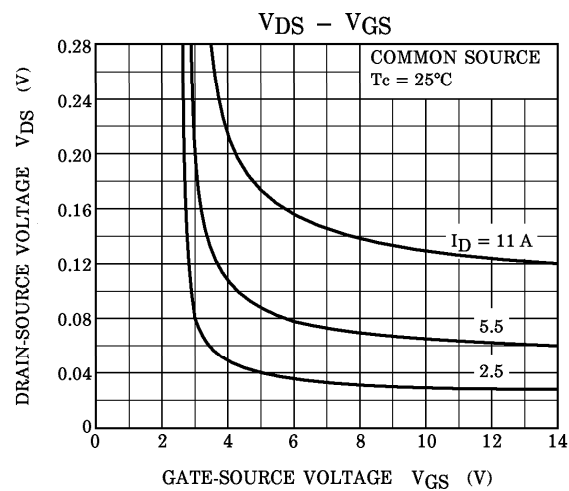
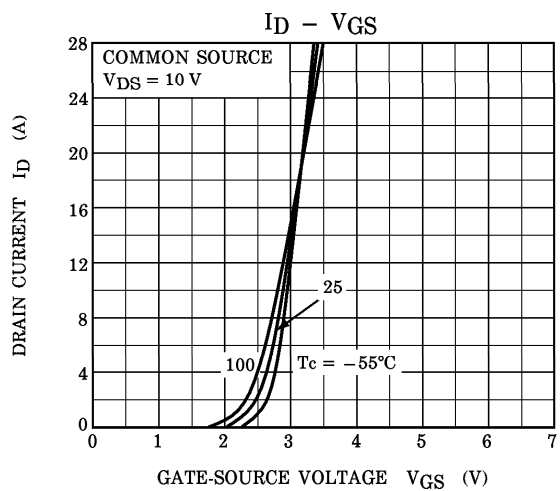
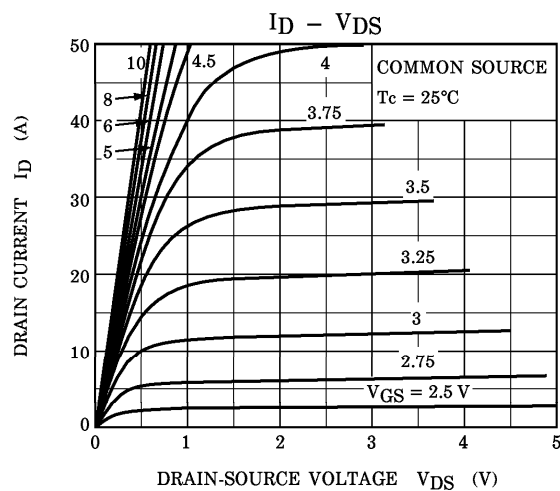
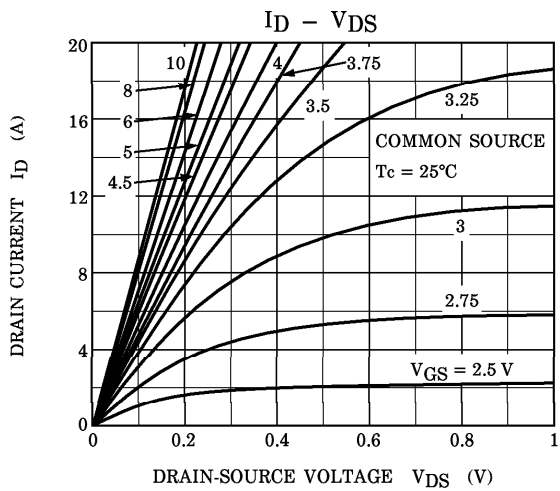
MARKING

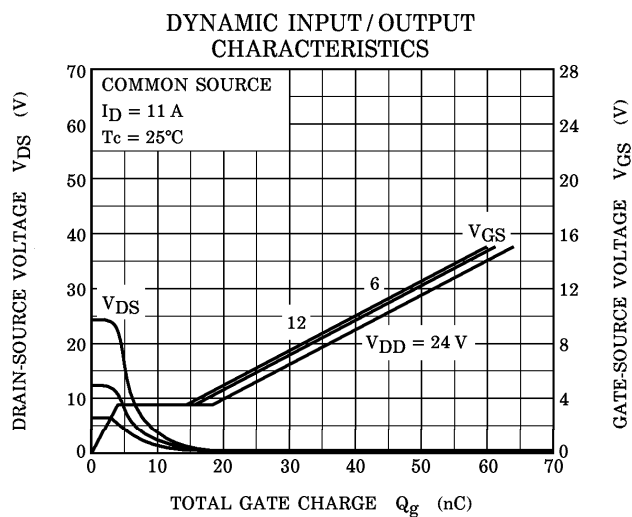
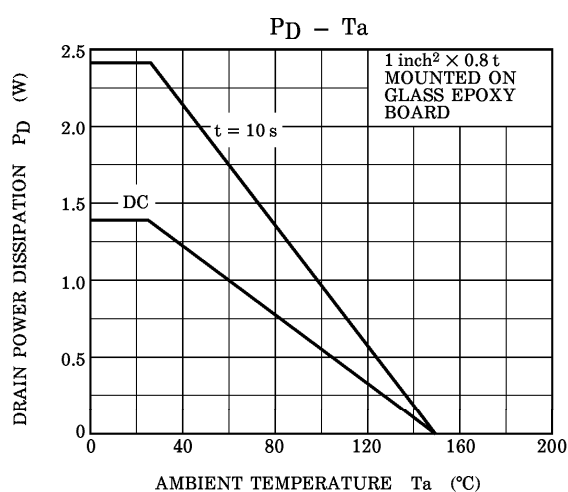
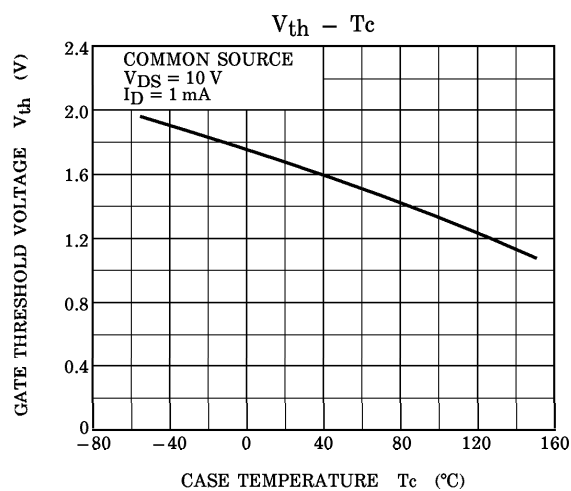
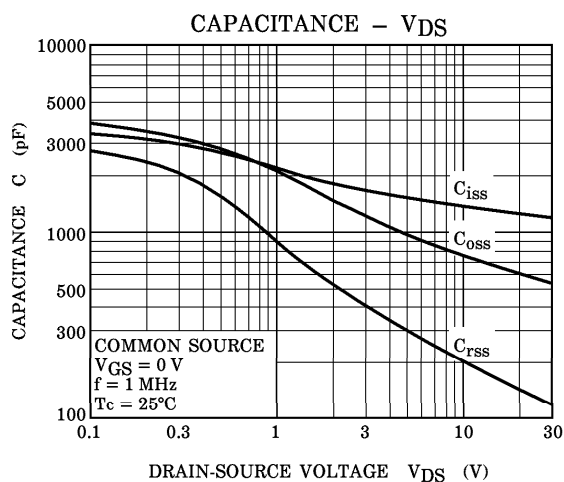
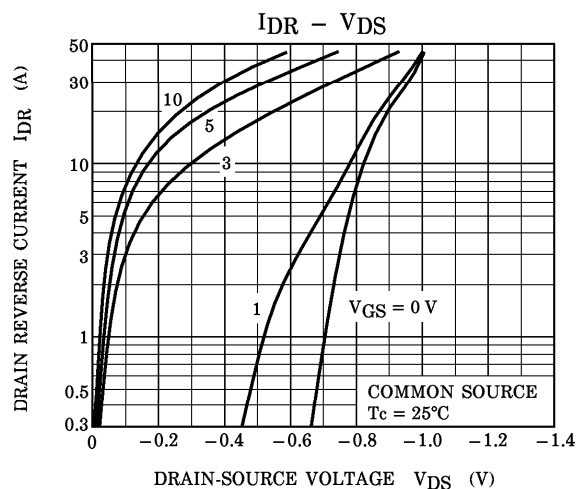
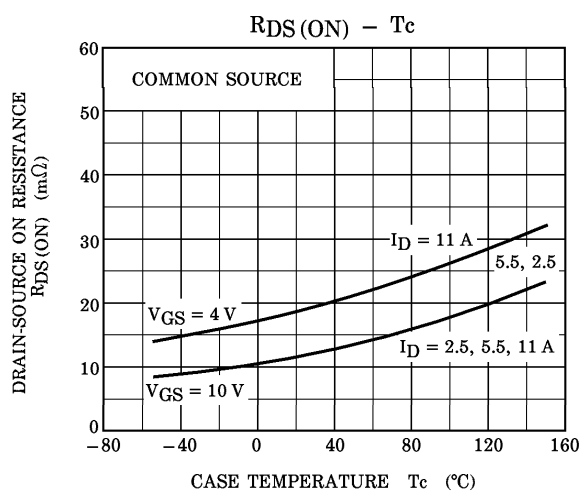


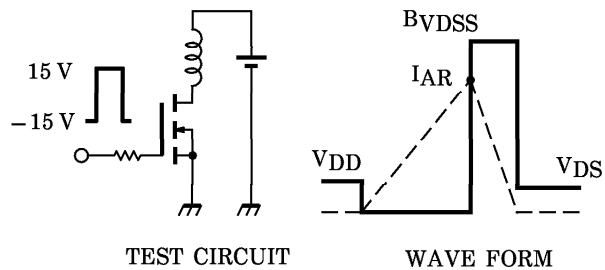
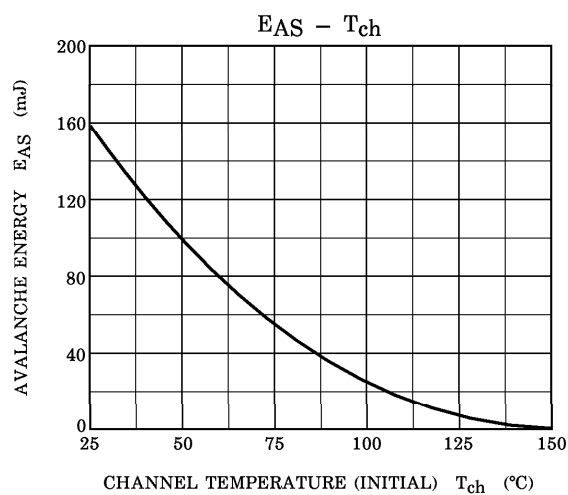
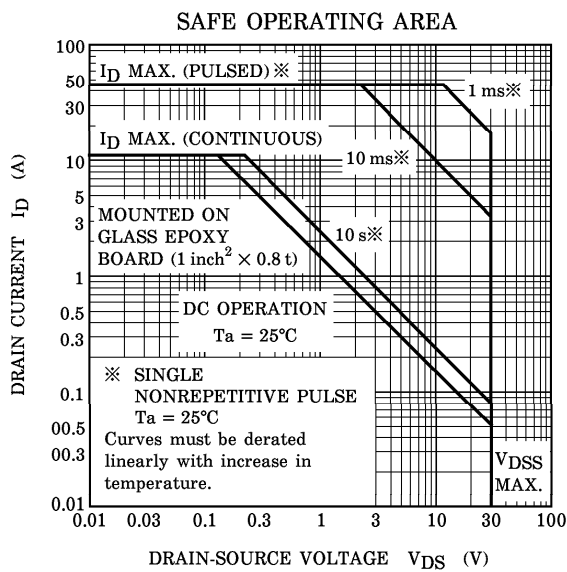
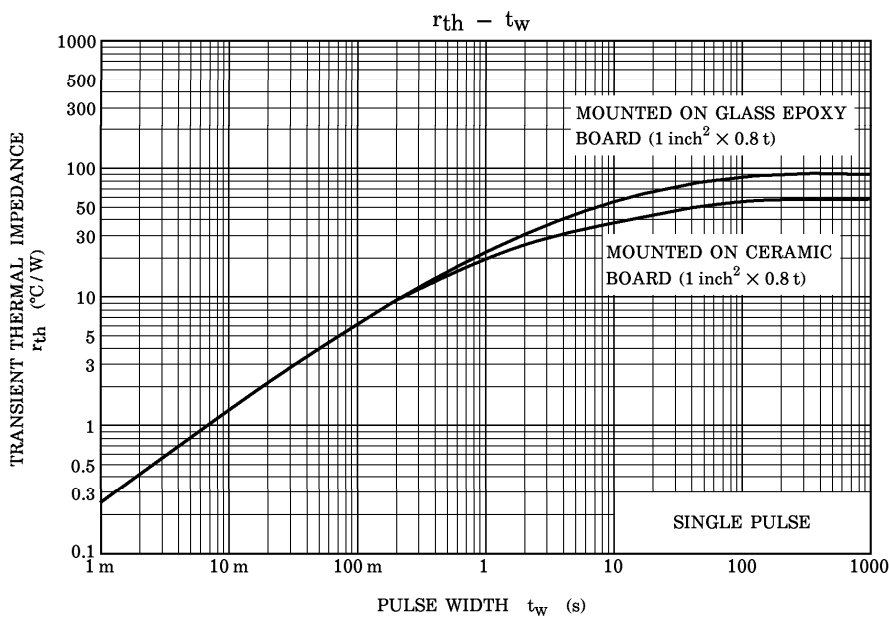
※ Lot Number


 Month (Starting from Alphabet A)


 Year (Last Number of the Christian Era)







Peak $I_{AR} = 11\text{ A}$, $R_G = 25\ \Omega$
 $V_{DD} = 24\text{ V}$, $L = 1.0\text{ mH}$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$